

10/728,706

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|--------|--|---|------------------|---------|------------------|
| L1 | 6 | TiN/Ti and @ad<"20021224" and ((aluminum al) same (copper cu)) and photoresist and (polyethylene PE) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/11 10:44 |
| L2 | 0 | ((polyethylene near10 thick\$4) same photoresist) and @ad<"20021224" and (metal near3 (line layer pattern)) and TiN/Ti | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/11 10:46 |
| L3 | 108 | ((polyethylene near10 thick\$4) same photoresist) and @ad<"20021224" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/11 11:17 |
| L4 | 0 | 3 and TiN/Ti | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/11 10:46 |
| L5 | 344640 | 3 (metal near3 (line layer pattern)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/11 10:47 |
| L6 | 27 | 3 and (metal near3 (line layer pattern)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/11 10:47 |
| L7 | 0 | ((polyethylene adj oxide) near10 thick\$4) same photoresist) and @ad<"20021224" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/11 11:17 |
| L8 | 1 | ((polyethylene adj oxide) near10 thick\$4) and photoresist and @ad<"20021224" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/11 11:18 |
| L9 | 51 | ((polyethylene adj oxide) same thick\$4) and photoresist and @ad<"20021224" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/11 12:31 |
| L10 | 775 | ((boron adj chloride) (boron adj trichloride)) same etch\$4) and @ad<"20021224" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/11 12:54 |

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|-----|----|--|---|----|-----|------------------|
| L11 | 11 | 10 and TiN/Ti | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/11 12:32 |
| L12 | 2 | ("6690084").PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2004/12/11 12:55 |
| L13 | 0 | 12 and ((boron adj chloride) (boron adj trichloride)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/11 12:55 |
| L14 | 0 | 12 and BCl3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/11 12:55 |
| S1 | 8 | ((("6316329") or ("6184148") or ("6006764") or ("5935762")).PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2004/12/11 09:48 |
| S2 | 1 | S1 and TiN/Ti | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/10 17:33 |
| S3 | 0 | (TiN/Ti near4 cap\$4) and Al/Cu and (TiN/Ti near4 barrier) and @ad<"20021224" and (metal adj (line layer pattern)) and photoresist | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/10 17:35 |
| S4 | 0 | (TiN/Ti same cap\$4) and Al/Cu and (TiN/Ti same barrier) and @ad<"20021224" and (metal adj (line layer pattern)) and photoresist | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/10 17:35 |
| S5 | 0 | (TiN/Ti same cap\$4) and Al/Cu and (TiN/Ti same barrier) and @ad<"20021224" and photoresist | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/10 17:36 |
| S6 | 3 | Al/Cu and TiN/Ti and @ad<"20021224" and photoresist | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/10 17:57 |

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| S7 | 1593 | (Al/Cu (aluminum and copper)) and @ad<"20021224" and photoresist and buffer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/10 18:03 |
| S8 | 106 | S7 and (ILD (interlayer adj dielectric)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/10 17:59 |
| S9 | 218 | (Al/Cu (aluminum and copper)) and @ad<"20021224" and (buffer same photoresist) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/10 18:04 |
| S10 | 138 | S9 and dielectric | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/10 18:05 |
| S11 | 136 | S10 and etch\$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/10 18:05 |
| S12 | 136 | S10 and etch\$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/10 18:10 |
| S13 | 332 | (metal adj line) and @ad<"20021224" and (insulation dielectric) and photoresist and buffer and etch\$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/10 18:12 |
| S14 | 80 | (metal adj line) and @ad<"20021224" and (insulation dielectric) and (photoresist same buffer) and etch\$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/10 18:12 |